



Phase Control Thyristor

Target Information

DS5499-1.2 February 2002

FEATURES

- Double Side Cooling
- High Surge Capability
- Low Inductance Internal Construction

APPLICATIONS

- High Power Converters
- DC Motor Control
- High Voltage Power Supplies

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{DRM} V	Conditions
DCR1660Y65	6500	$T_{v_i} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1660Y64	6400	$I_{DRM} = I_{RRM} = 150 \text{mA},$
DCR1660Y63	6300	V_{DRM} , V_{RRM} $t_p = 10ms$,
DCR1660Y62	6200	V_{DSM} & V_{RSM} =
DCR1660Y61	6100	V _{DRM} & V _{RRM} + 100V
DCR1660Y60	6000	respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1660Y63

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

V_{DRM}		6500V
T(AV)		1665A
I _{TSM}	(max)	28000A
dV/dt		1000V/μs
dl/dt		300Α/ μ s

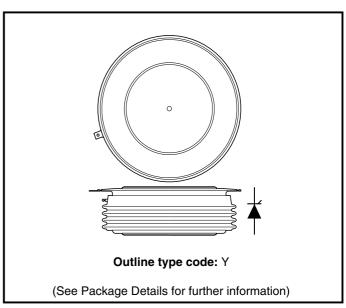


Fig. 1 Package outline



CURRENT RATINGS

$T_{case} = 60^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions		Units				
Double Side	Double Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1665	Α				
I _{T(RMS)}	RMS value	-	2600	Α				
I _T	Continuous (direct) on-state current	-	2478	Α				
Single Side Cooled								
I _{T(AV)}	Mean on-state current	Half wave resistive load	1112	Α				
I _{T(RMS)}	RMS value	-	1746	Α				
I _T	Continuous (direct) on-state current	-	1556	Α				

$T_{case} = 80^{\circ}C$ unless stated otherwise.

Symbol	Parameter	meter Test Conditions		Units				
Double Sid	Double Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1323	Α				
I _{T(RMS)}	RMS value	-	2077	Α				
I _T	Continuous (direct) on-state current	-	1944	А				
Single Side	Single Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	876	Α				
I _{T(RMS)}	RMS value	-	1376	Α				
I _T	Continuous (direct) on-state current	-	1196	Α				



SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	22.0	kA
l²t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	2.4 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	28.0	kA
l²t	I ² t for fusing	V _R = 0	3.92 x 10 ⁶	A²s

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditi	Test Conditions		Max.	Units
I _{RRM} /I _{RRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125	At V _{RRM} /V _{DRM} , T _{case} = 125°C		300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C	;	-	1000	V/μs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} ,	Repetitive 50Hz	-	150	A/μs
		Gate source 30V, 15 Ω ,	Non-repetitive	-	300	A/μs
		t _r ≤ 0.5μs, T _j = 125°C				
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C	At T _{vj} = 125°C		1.2	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.61	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 15 Ω		0.5	1.5	μs
		$t_{r} = 0.5 \mu s, T_{j} = 25^{\circ} C$				
t _q	Turn-off time	$I_{T} = 1000A, t_{p} = 1 ms, T_{j} = 1 ms$	=125°C,	1500	-	μs
		$V_{R} = 100V, dI_{RR}/dt = 10A/\mu s,$				
		$V_{DR} = 67\% V_{DRM}$				
		$dV_{DR}/dt = 25V/\mu s$ linear				
I	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 10V$		-	600	mA
I _H	Holding current	$T_j = 25^{\circ}C$, $V_{G-K} = \infty$		-	200	mA



THERMAL AND MECHANICAL RATINGS

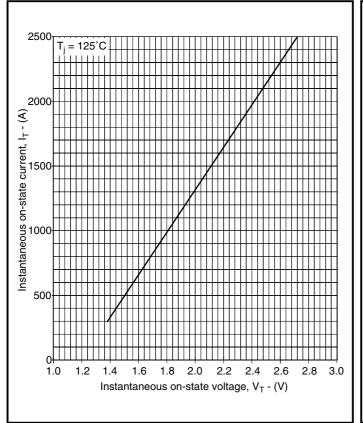
Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	DC	-	0.0095	°CW
		Single side cooled	Anode DC	-	0.019	°CW
			Cathode DC	-	0.019	°CW
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 50kN	Double side	-	0.002	°CW
		(with mounting compound)	Single side	-	0.004	°CW
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T_{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			45.0	55.0	kN

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.0	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	300	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V _{RGM}	Peak reverse gate voltage	-	5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	10	А
P _{GM}	Peak gate power	See table fig. 4	150	W
P _{G(AV)}	Mean gate power	-	5	W



CURVES



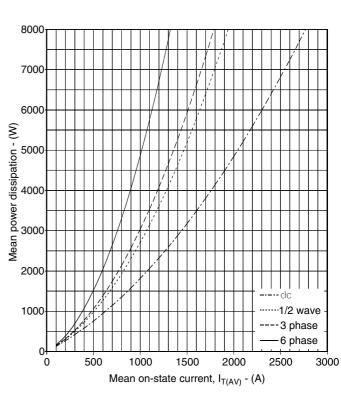


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Power dissipation



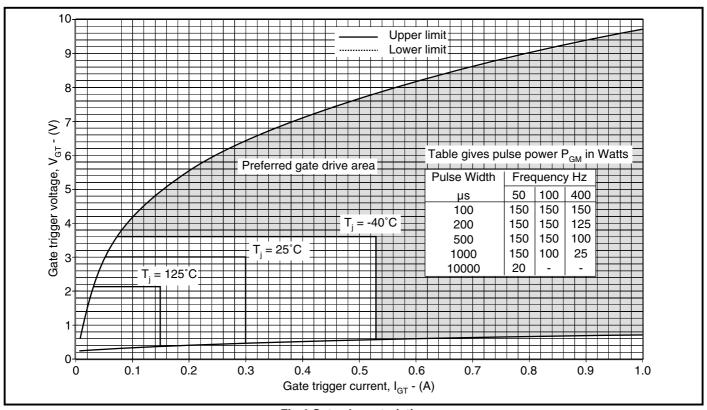


Fig.4 Gate characteristics

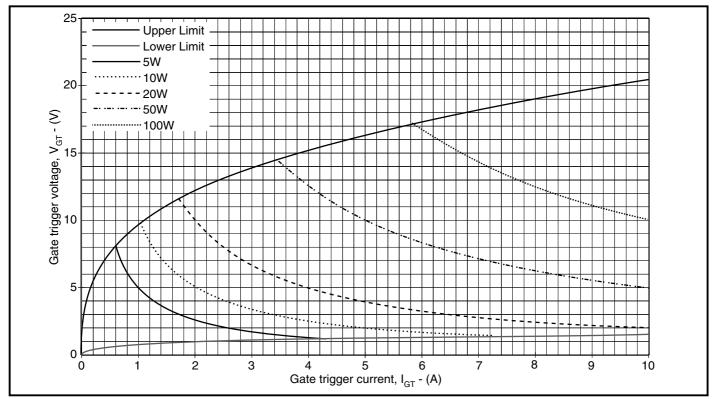
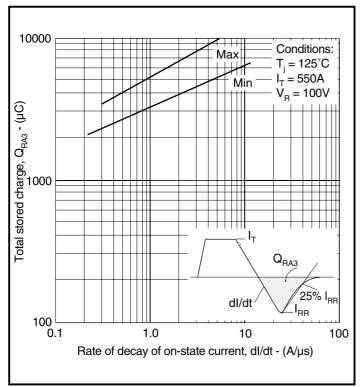


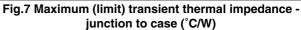
Fig.5 Gate characteristics

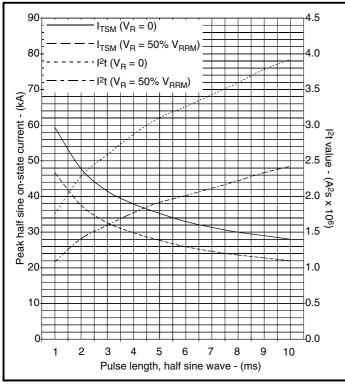




0.1 Double side cooled Effective thermal resistance Conduction Junction to case ${^\circ\text{C/W}}$ Double side Anode side 0.0095 0.0105 0.019 3 phase 120° 6 phase 60° 0.0112 0.0207 0.0234 0.0001 0.001 0.01 0.1 10 100 Time - (s)

Fig.6 Stored charge







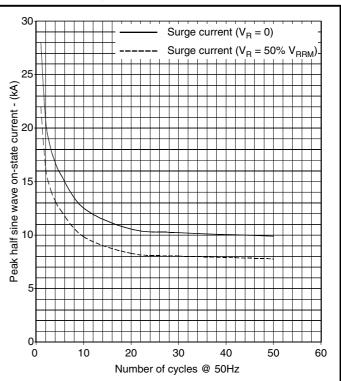
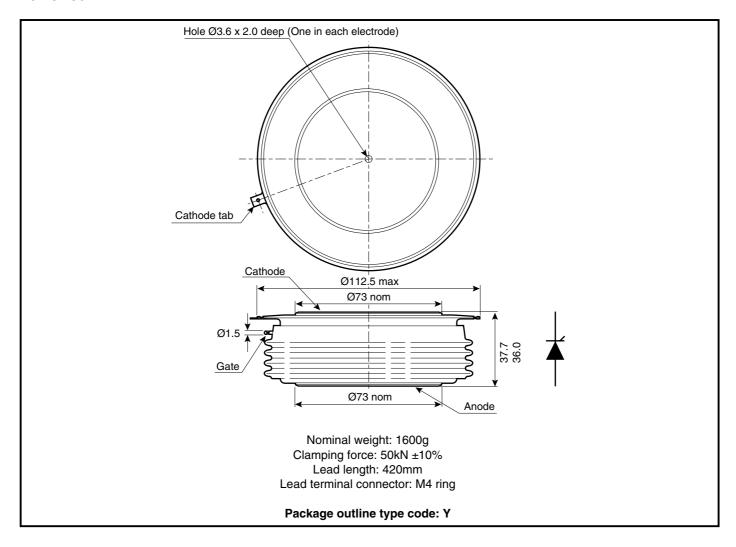


Fig.9 Multi-cycle surge currents



PACKAGE DETAILS

For further package information, please contactCustomer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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